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(54) **Title:** INTEGRATED CAPACITIVELY COUPLED PLASMA AND REMOTE INDUCTIVELY COUPLED PLASMA

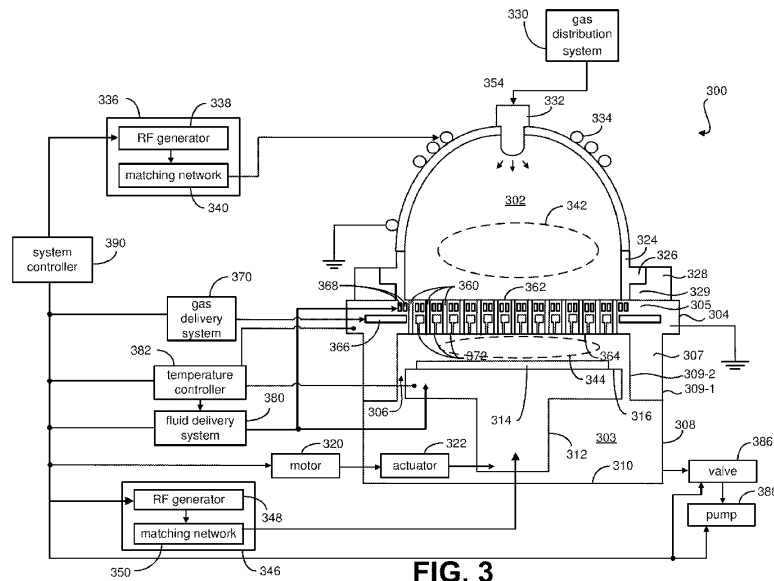


FIG. 3

(57) **Abstract:** A plasma processing apparatus integrates an inductively-coupled plasma (ICP) chamber and a capacitively-coupled plasma (CCP) chamber. The ICP chamber is in fluid communication with the CCP chamber via a showerhead that is positioned between the ICP chamber and CCP chamber. A substrate is supported on a pedestal in the CCP chamber. The ICP chamber generates remote plasma in the ICP chamber and the CCP chamber generates direct plasma in an environment adjacent to the substrate. In some implementations, the remote plasma generated by the ICP chamber may assist in deposition of a first layer on the substrate and the direct plasma generated by the CCP chamber may assist in etch or treatment of the first layer, or deposition of a second layer on the substrate without necessitating transfer of the substrate between modules or stations.

[Continued on next page]

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